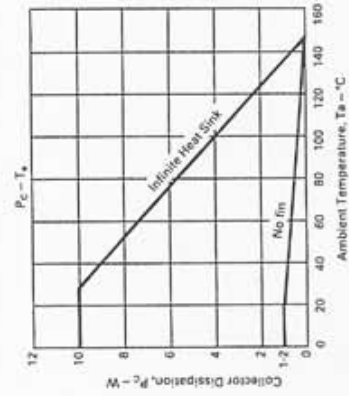
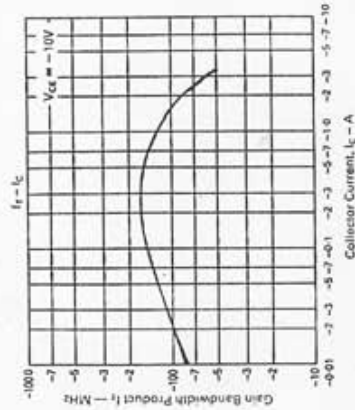
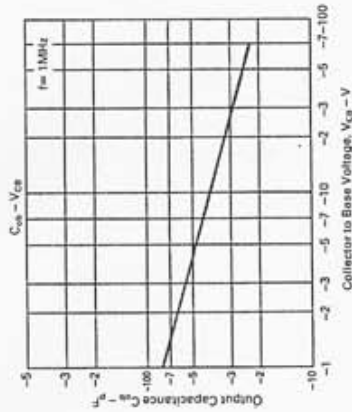
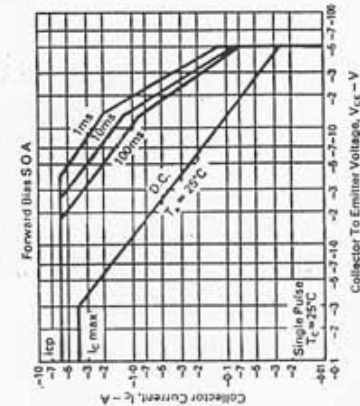




NEW PRODUCT

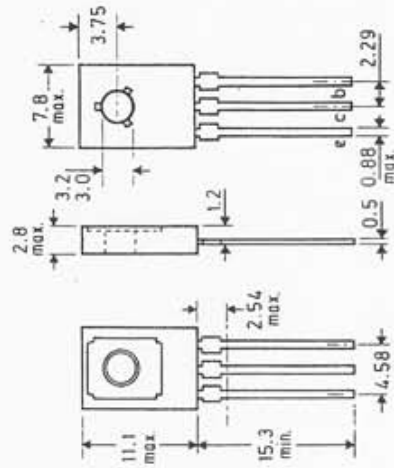
BUP 40



SILICON PNP
EPITAXIAL PLANAR

MECHANICAL DATA

Dimensions in mm



TO 126

FEATURES

- VERY LOW $V_{CE(sat)}$
- HIGH GAIN AT HIGH CURRENT
- VERY FAST SWITCHING
- NPN COMPLEMENT BUP 41

ABSOLUTE MAXIMUM RATINGS

V_{CEO}	Collector-base voltage ($I_E = 0$)	-60V
V_{ECO}	Collector-emitter voltage ($I_B = 0$)	-50V
V_{EBO}	Emitter-base voltage ($I_C = 0$)	-6V
I_C	Collector current	-6A
P_{MH}	Total power dissipation at $T_{case} \leq 25^\circ C$	-10W
T_{stg}	Storage temperature	-55 to 150°C
T_J	Junction temperature	150°C

SEMELAB LTD., TELEPHONE: (0455) 554711. TELEX: 341927. FAX: (0455) 552612

TENTATIVE E/S0

ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise specified)

Parameter	Test Conditions	Min. Typ. Max	Unit
I _{CEO}	V _{CB} = -40V	-1	μA
I _{EB0}	V _{EB} = -4V	-1	μA
V _{CE(sat)} *	I _C = -3A I _B = -0.1A	-1.1	V
V _{BE(sat)} *	I _C = -3A I _B = -0.1A	-1.4	V
h _{FE1} *	I _C = -1A V _{CE} = -2V	100	—
h _{FE2} *	I _C = -5A V _{CE} = -5V	200	—
f _T	I _C = -1A V _{CE} = -5V	150	MHz
C _{CB0}	V _{CB} = -10V f = 1MHz	40	pf
I _{SB}	V _{CE} = -18V t = 1 m sec	-1	A

* Pulsed; pulse duration = 300μs, duty cycle = 1-5%

